

Akademia Górniczo-Hutnicza im. Stanisława Staszica w Krakowie

AGH UNIVERSITY OF SCIENCE AND TECHNOLOGY

Disorder and transport properties of (Co,Cu,Mg,Ni,Zn)O high entropy oxide

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High entropy materials – historical outline

High entropy materials – materials, the structure of which is stabilized by high configurational entropy.

2004 – High entropy alloys

•B. Cantor, I. T. Chang, P. Knight and A. J. Vincent, Microstructural development in equiatomic multicomponent alloys. Materials Science and Engineering: A 2004 Vol. 375-377 pp. 213-218

•J. W. Yeh, S. K. Chen, S. J. Lin, J. Y. Gan, T. S. Chin, T. T. Shun, C. H. Tsau and S. Y. Chang, Nanostructured high-entropy alloys with multiple principal elements: novel alloy design concepts and outcomes. Advanced Engineering Materials 2004 Vol. 6 pp. 299-303

2015 – High entropy oxides

C. M. Rost, R. Schaet, T. Borman, A. Moballegh, E. C. Dickey, D. Hou, J. L. Jones, S. Curtarolo and J. P. Maria, Entropy-stabilized oxides. Nature Communications 2015 Vol. 6 pp. 8485



High entropy alloys – alloys created by mixing at least 5 elements together in approximately identical amounts (5-35% at.). Metal atoms are randomly located in high entropy alloys. The configurational entropy of such a system achieves its maximum value in the case of a solid solution, which facilitates the formation of simple crystalline structures.

High entropy oxides – oxides that constitute a solid solution consisting of at least 5 metal oxides. These materials are interesting due to their transport properties that manifest through e.g. high ionic conductivity. Potential applications:

Lithium batteries, solid oxide fuel cells (SOFC)



High entropy oxides may have practical use due to the point defect structure and mobility of these oxides.

Becoming familiar with the transport properties of these materials will enable the possibility of maximizing their hidden potential and making them a valuable group of new materials that constitute a basis for future energycreating technology.





Experimental procedure

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Initial materials for investigations (powders):
Co<sub>3</sub>O<sub>4</sub>, CuO, MgO, NiO, ZnO,
purity > 99,9 % at.; granulation 0,044 ÷ 0,250 µm
Milling:
90 min, 600 rot/s, planetary mill (Fritsch Pulverisette 7)
Pressing:
dics: \Phi = 10 mm, h = 2 mm, pressure: 2 t
Sintering:
20 h, 1273 K, cooling on a cold aluminium plate
Microstructural studies:
XRD, SEM+EDS
Marker investigations:
Au, 1173 K,
Deviation from stoichiometry studies:
1173 K, 10-10<sup>5</sup> Pa (thermogravimetric method)
Chemical diffusion investigations:
1173 K, 10-10<sup>5</sup> Pa (re-equilibration method)
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Z. Grzesik, A. Poczekajlo, G. Smola, S. Mrowec, "Marker method in studying the defect structure in products of the oxidation of highly disordered substrates", High Temperature Materials and Processes, <u>35</u>, 21-28 (2016)







Z. Grzesik, A. Poczekajlo, G. Smola, S. Mrowec, "Marker method in studying the defect structure in products of the oxidation of highly disordered substrates", High Temperature Materials and Processes, <u>35</u>, 21-28 (2016)

Modified marker method Oxidation of (Co,Cu,Mg,Ni,Zn)O oxide

Assumption:

Predominant disorder is present in the cation sublattice



Data:

Sample parameters after heating (1173 K, p_{O2} = 10 Pa): mass = 0,4336 mg diameter = 10 mm height = 1,57 mm

Sample mass change after oxidation (1173 K, p_{O2} = 10⁵ Pa): 7 mg

 $h = 12 \ \mu m$

Conclusion:

In the case of predominant disorder in the cation sublattice, markers should be located 12 micrometers below the oxide surface.



Necessary conditions for obtaining positive results by means of the modified marker method

- Before marker deposition, the oxide sample must be heated under <u>lower</u> oxygen pressure compared to the pressure used during oxidation of the sample covered with markers.
- The change in deviation from stoichiometry of a studied oxide during a marker experiment must be large (order of a few percent).
- Sample thickness should exceed 1 mm.
- The duration of defect concentration re-equilibration during oxygen pressure changes should be several times longer than ~1 min (this means that the chemical diffusion coefficient is low and/or the sample thickness is large).

Conclusion:

A full interpretation of a modified marker experiment is possible after completing both marker studies, as well as point defect concentration and mobility investigations inside a given oxide.



Determining deviation from stoichiometry in MeX_{1-y} -type oxides using the gravimetric method when the metal content in the sample is known

$$y = 1 - \frac{m_O M_{Me}}{m_{Me} M_O}$$

where:

 m_{Me} – mass of the metal in an oxide sample m_O – oxygen mass in an oxide sample M_{Me} i M_O – atomic masses of metal and oxygen.



Scheme of the correlation between defect concentration and oxidant pressure in an oxide with a complex defect structure



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p^{*} - oxygen pressure, at which $Co_{3\pm y}O_4$ oxide is strictly stoichiometric (y = 0)

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Z. Grzesik, A. Kaczmarska, "Defect structure of Co_3O_4 cobalt oxide", Ann. Chim. Sci. Mat. <u>40 (1-2)</u>, 103-109 (2016).

$Co_{3\pm y}O_4$ sample mass changes and deviation from stoichiometry, y, as a function of oxygen pressure



Assumption:

 $m = f(\ln p)$ and $y = f(\ln p)$ curves exhibit an inflection point for p^*

$$p = p^* = \left(\frac{a}{b}\right)^{\frac{3}{4}}$$

Proof:

The second derivative of $m = f(\ln p)$ and $y = f(\ln p)$ is equal to zero for p^{*} and in the vicinity of p^{*} both functions change their sign

$$\frac{d^2y}{d(\ln p)^2} = 0 \quad \Rightarrow \quad b \cdot p^{\frac{2}{3}} - a \cdot p^{-\frac{2}{3}} = 0 \quad \Rightarrow \quad p = p^* = \left(\frac{a}{b}\right)^{\frac{3}{4}}$$

$$m = m^* + \frac{4}{3}M_0 \cdot b \cdot p^{\frac{2}{3}} - \frac{4}{3}M_0 \cdot a \cdot p^{-\frac{2}{3}}$$

where m^* denotes the mass of a stoichiometric Co_3O_4 , and M_0 is the atomic mass of oxygen

$$\frac{d^2 \Delta m}{d(\ln p)^2} = \frac{4}{3} M_0 \cdot \left(\frac{4}{9} b \cdot p^{\frac{2}{3}} - \frac{4}{9} a \cdot p^{-\frac{2}{3}} \right) = 0 \implies p = p^* = \left(\frac{a}{b} \right)^{\frac{3}{4}}$$

Z. Grzesik, A. Kaczmarska, "Defect structure of Co_3O_4 cobalt oxide", Ann. Chim. Sci. Mat. <u>40 (1-2)</u>, 103-109 (2016).

Oxidant pressure dependence of defect concentration in an oxide with a simple defect structure



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Determining chemical diffusion coefficients of defects by means of re-equilibration technique

$$\tilde{D}t/a^2 < 0.25$$
:
 $\left(\frac{\Delta m_t}{\Delta m_k}\right)^2 = \frac{4\tilde{D}t}{\pi a^2}$

$$\widetilde{D}t/a^2 > 0.15:$$

$$1 - \frac{\Delta m_t}{\Delta m_k} = \frac{8}{\pi^2} \exp\left(-\frac{\widetilde{D}\pi^2 t}{4a^2}\right)$$

where:

- Δm_t sample mass change after duration t
- Δm_k total sample mass change
- a half of the sample thickness
- D chemical diffusion coeffcient

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Temperature dependence of chemical diffusion coefficients in selected metal oxides and sulphides







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